

CMP048N04/CMB048N04/CMI048N04/CMF048N04

40V, 4mΩ typ., 120A N-Channel MOSFET

General Description

The 048N04 uses advanced SGT technology to provide excellent RDS(ON). It can be used in a wide variety of applications.

Product Summary

BVDSS	R _{DS(on)} max.	ID
40V	4.6mΩ	120A

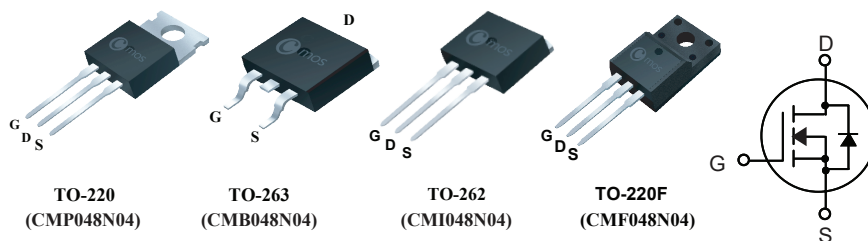
Applications

- Motor control and drive
- Battery management

Features

- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

TO-220/263/262/220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	220/263/262	220F	Units
V _{DS}	Drain-Source Voltage	40		V
V _{GS}	Gate-Source Voltage	±20		V
I _D @T _C =25°C	Continuous Drain Current	120	120*	A
I _D @T _C =100°C	Continuous Drain Current	84	84*	A
I _{DM}	Pulsed Drain Current	480	480*	A
EAS	Single Pulse Avalanche Energy (Note 1)	182		mJ
P _D @T _C =25°C	Total Power Dissipation	130	38	W
T _{STG}	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C

* Drain current limited by maximum junction temperature.

Thermal Data

Symbol	Parameter	220/263/262	220F	Unit
R _{θJA}	Thermal Resistance Junction-ambient Max.	62.5	62.5	°C/W
R _{θJC}	Thermal Resistance Junction-case Max.	0.96	3.29	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	4	4.6	mΩ
		$V_{GS}=4.5V$, $I_D=10A$	---	4.9	6	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V$, $V_{GS}=0V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	±100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=10A$	---	27	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.8	---	Ω
Q_g	Total Gate Charge	$V_{DD}=20V$, $I_D=50A$ $V_{GS}=4.5V$	---	16	---	nC
Q_{gs}	Gate-Source Charge		---	6	---	
Q_{gd}	Gate-Drain Charge		---	4.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=20V$, $I_D=50A$, $R_L=0.4\Omega$ $R_G=10\Omega$, $V_{GS}=10V$	---	13	---	ns
T_r	Rise Time		---	7.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	65	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1800	---	pF
C_{oss}	Output Capacitance		---	370	---	
C_{rss}	Reverse Transfer Capacitance		---	30	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	120	A
I_{SM}	Pulsed Source Current		---	---	480	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=20A$	---	0.85	1.2	V

Note :

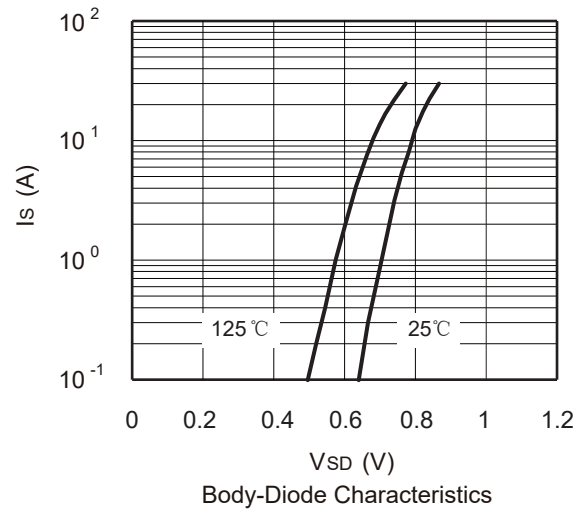
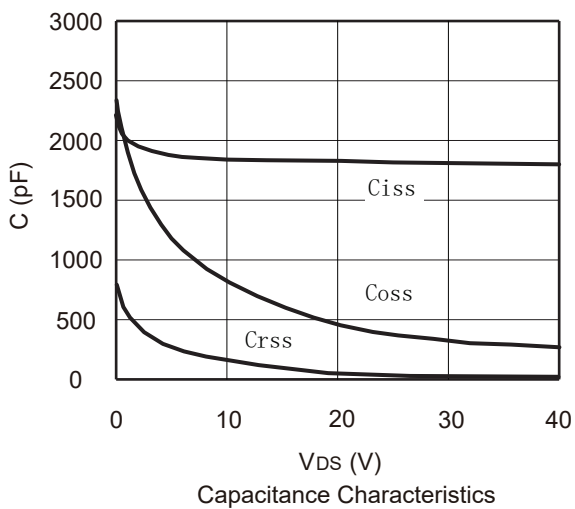
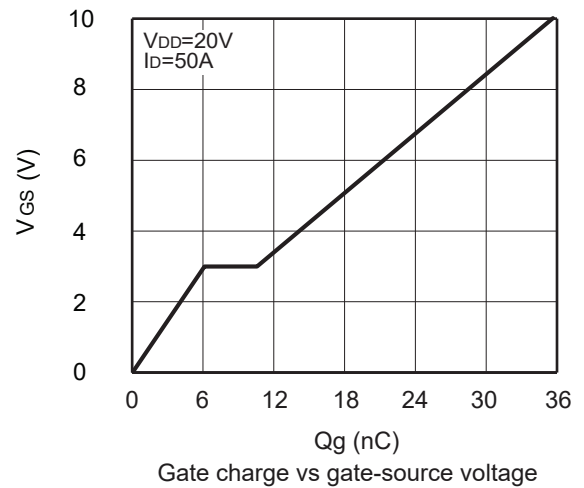
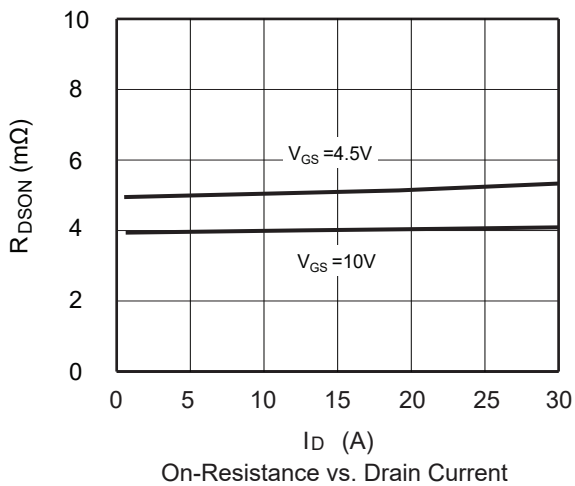
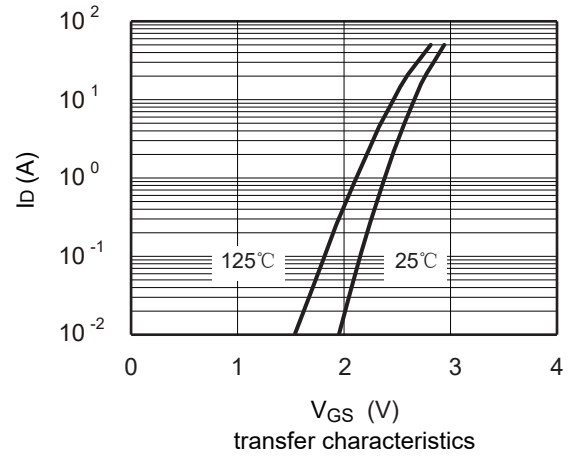
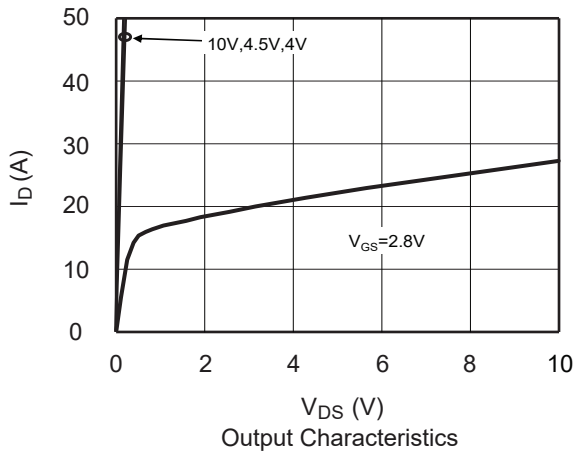
1.The EAS data shows Max. rating .The test condition is $V_{DS}=30V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=27A$.

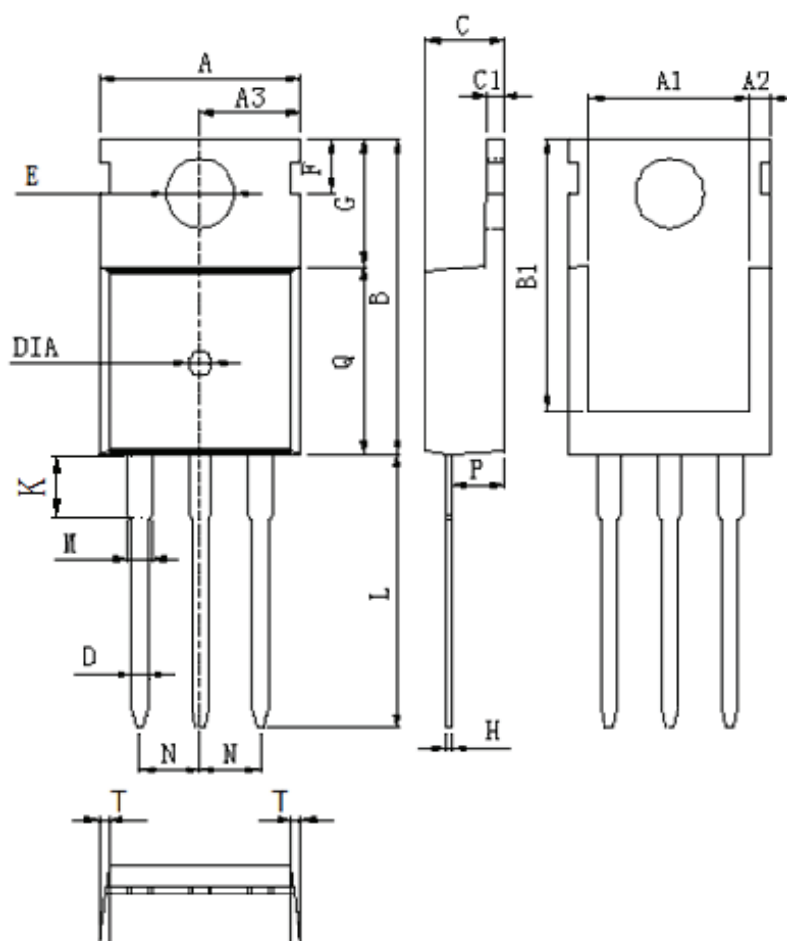
This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

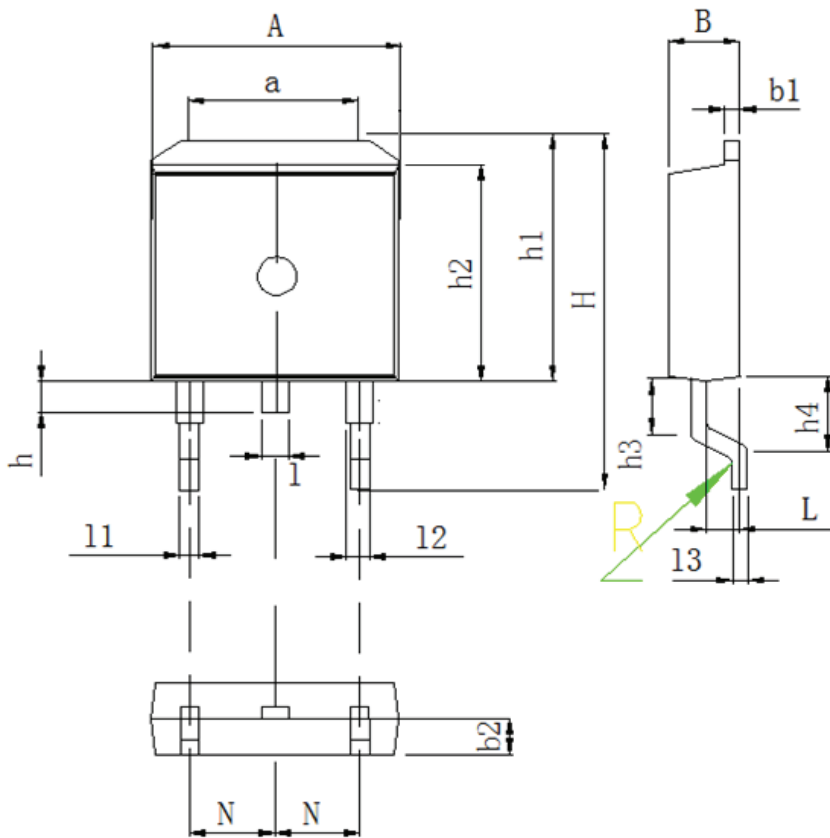
Cmos reserves the right to improve product design , functions and reliability without notice.Please refer to the latest version of specification.

Typical Characteristics

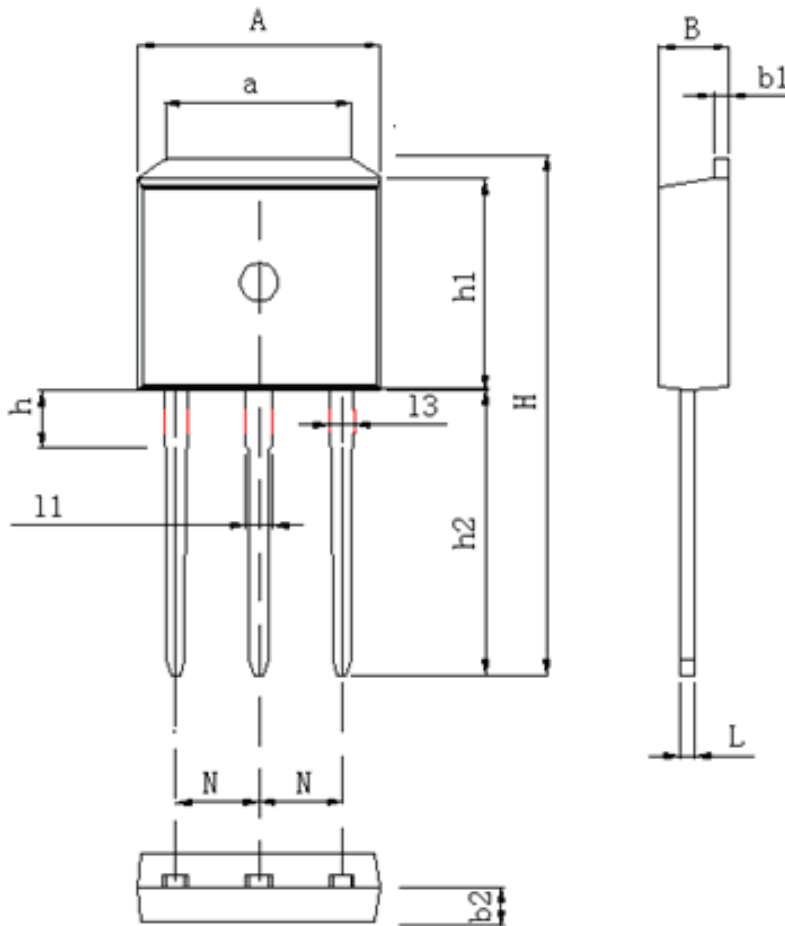


Package Dimension
TO-220
Unit :mm


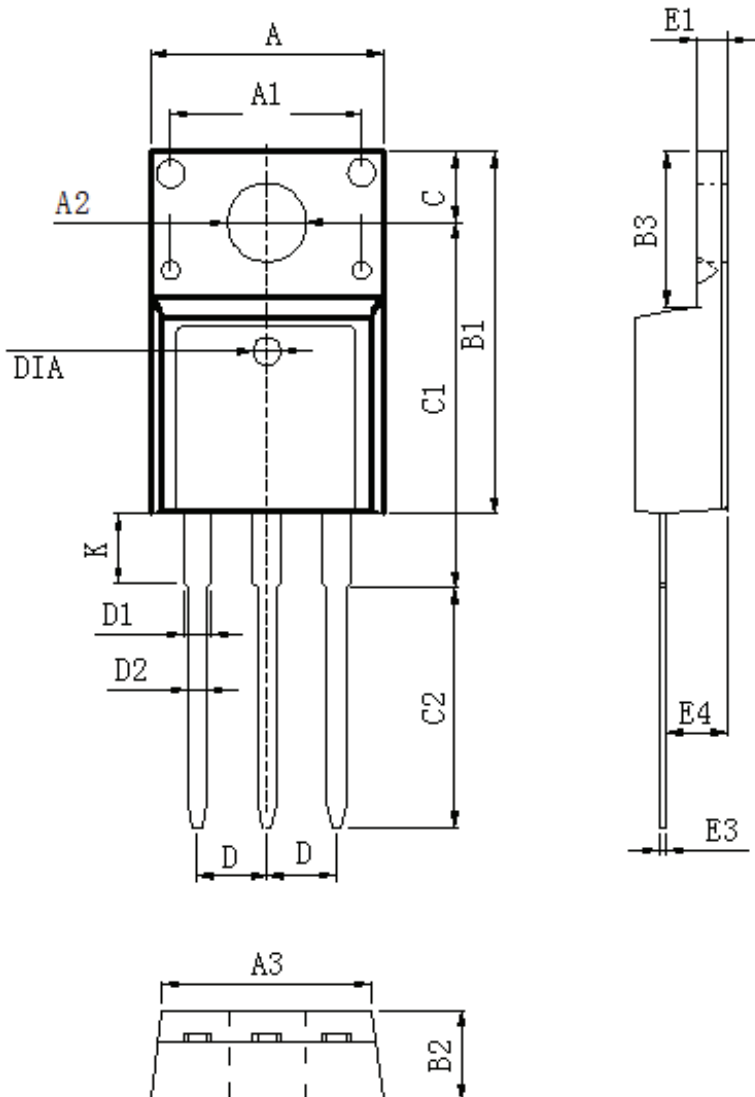
DIM	MILLIMETERS
A	10.0 ± 0.3
A1	8.64 ± 0.2
A2	1.15 ± 0.1
A3	5.0 ± 0.2
B	15.8 ± 0.4
B1	13.2 ± 0.3
C	4.56 ± 0.1
C1	1.3 ± 0.2
D	0.8 ± 0.2
E	3.6 ± 0.2
F	2.95 ± 0.3
G	6.5 ± 0.3
H	0.5 ± 0.1
K	3.1 ± 0.2
L	13.2 ± 0.4
M	1.25 ± 0.1
N	2.54 ± 0.1
P	2.4 ± 0.3
Q	9.0 ± 0.3
T	W:0.35
DIA	⊙1.5 (deep 0.2)

Package Dimension
TO-263
Unit :mm


DIM	MILLIMETERS
A	9.8 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	15.5 ± 0.3
h	1.54 ± 0.2
h1	10.5 ± 0.2
h2	9.2 ± 0.1
h3	1.54 ± 0.2
h4	2.7 ± 0.2
L	2.4 ± 0.2
1	1.3 ± 0.1
11	0.8 ± 0.1
12	1.3 ± 0.1
13	0.5 ± 0.1
N	2.54 ± 0.1
R	$0.5R \pm 0.05$

Package Dimension
TO-262
Unit :mm


DIM	MILLIMETERS
A	9.98 ± 0.2
a	7.4 ± 0.4
B	4.5 ± 0.2
b1	1.3 ± 0.05
b2	2.4 ± 0.2
H	23.9 ± 0.3
h	3.1 ± 0.2
h1	9.16 ± 0.2
h2	13.2 ± 0.2
L	0.5 ± 0.1
l1	1.3 ± 0.1
l2	0.8 ± 0.1
N	2.45 ± 0.1

Package Dimension
TO-220F
Unit :mm


DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.87±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	2.54±0.1
E3	0.5±0.1
E4	2.76±0.2
DIA	⌀1.5 (deep 0.2)